



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/632,186 Filing Date: July 30, 2003
Confirmation No.: 3961
First Named Inventor: Yi Ding
Assignee: ProMOS Technologies, Inc.
Examiner: Nguyen, Thanh T. Art Unit: 2813
Attorney Docket No.: M-15241 US

San Jose, California
February 11, 2005

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

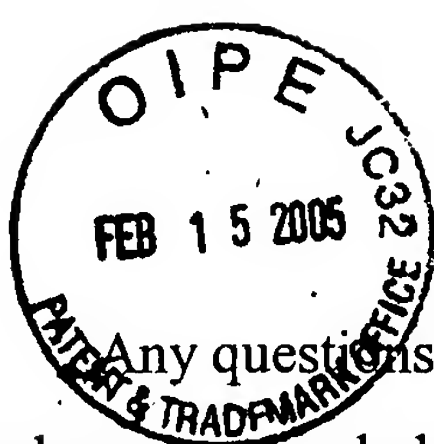
COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Dear Sir:

The Examiner's Statement of Reasons for Allowance states:

Claims 1-9, 20-49 are allowed because none of the prior art ... teaches or suggests the particular subset of the process steps in forming a nonvolatile memory by forming a layer to provide at least two conductive floating gates for the memory cell, ... wherein the memory cell comprises two source/drain and a channel region which borders on the source/drain regions, and each floating gate ... is operable to control a portion of the channel region.

The claim language referred to above does not appear in some of the independent claims. See in particular Claims 2, 5, 9, 46, 48. These claims are believed to be allowable for the reasons given in Applicant's Amendment filed on October 12, 2004.



Any questions regarding this case can be addressed to the undersigned at the telephone number below.

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on February 11, 2005.

Michael Shenker 2-11-05
Attorney for Applicant(s) Date of Signature

Respectfully submitted,

Michael Shenker

Michael Shenker

Patent Attorney

Reg. No. 34,250

Telephone: (408) 392-9250, Ext. 212

Law Offices Of

MacPherson Kwok Chen & Heid LLP

1762 Technology Drive, Suite 226

San Jose, CA 95110